

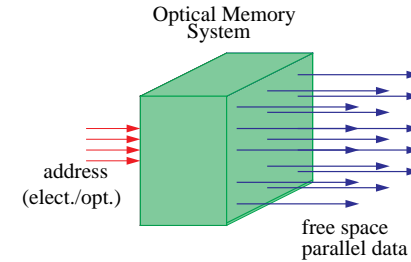
Optoelectronic Cache Memory System Architectures

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Motivation

Optical memory as an alternative to disks and disk arrays as a backing store for a hierarchical memory system in a general purpose computer

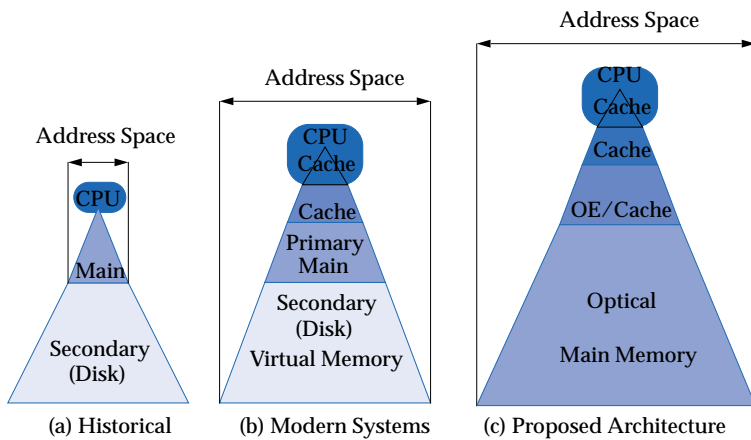


Generic Specifications (near term optical memory device):

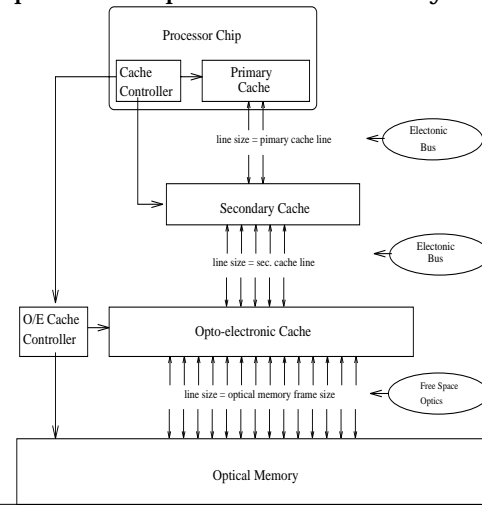
- Multi-Terabit Capacity
- 1Mbit free space optical I/O
- 1μs Access Latency



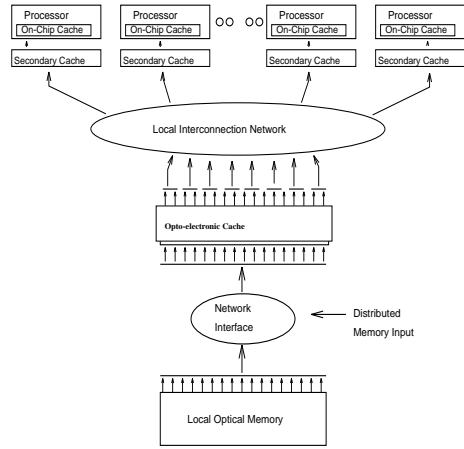
Memory Hierarchy Evolution



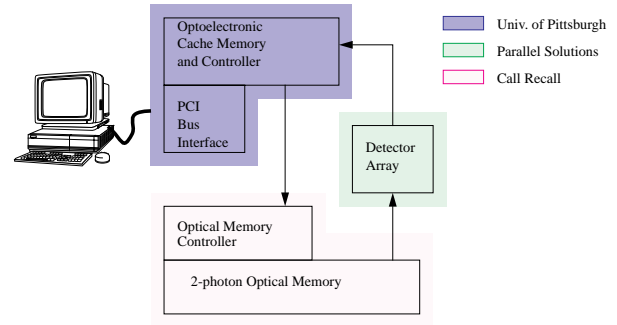
Uniprocessor Optoelectronic Memory Hierarchy



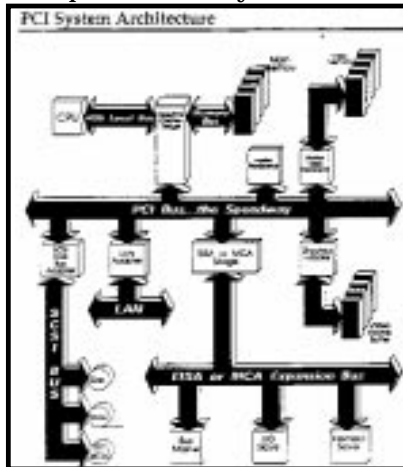
Multiprocessor Optoelectronic Memory Hierarchy



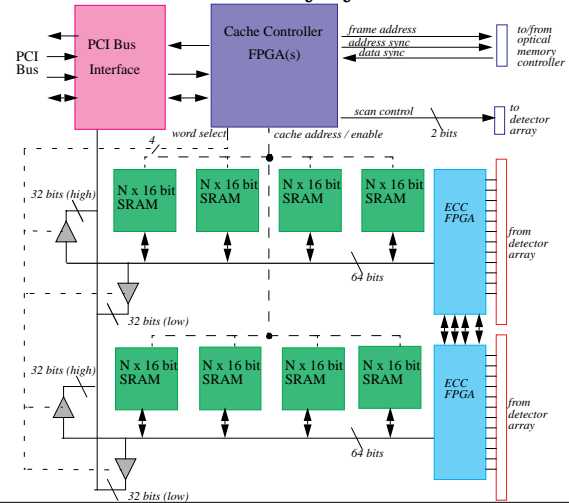
Block Diagram Organized by Participating Research Groups



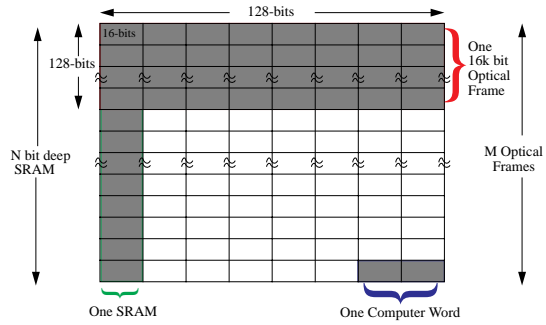
Computer Memory Architecture



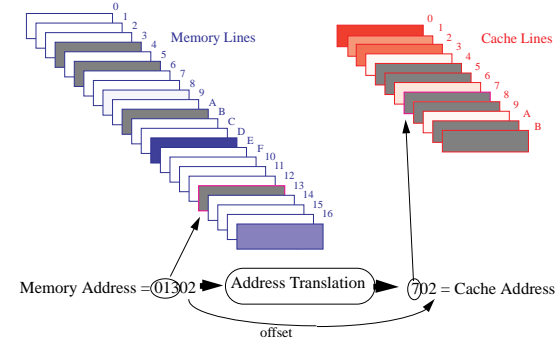
Cache Memory System



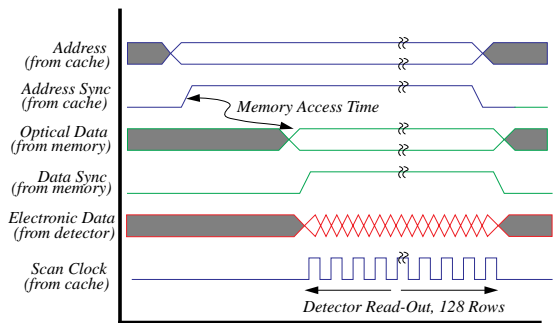
Logical Relationship of Optical Memory to Cache Organization



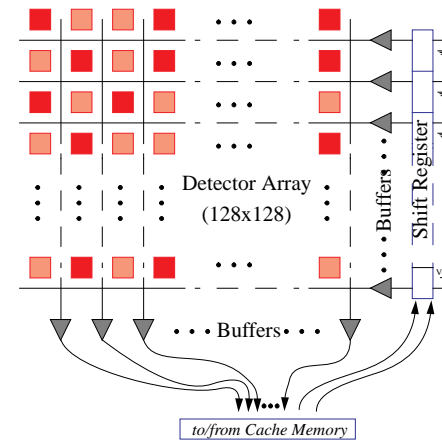
Address Translation Between Memory Line 13 and Cache Line 07, offset of 02 is preserved across the translation

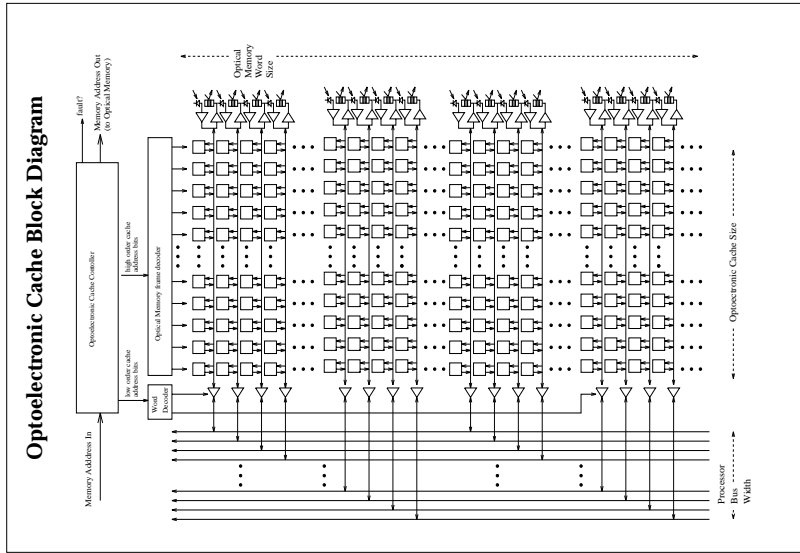


System Timing



Detector Array Organization





Simulation Studies

Three applications

- Image Convolution
- Matrix Multiply
- Heap Sort
-

Three level memory hierarchy - Two Models

- Model 1: Electronic Main Memory/ Disk Backing Store
- Model 2: Optoelectronic Cache/Optical Backing Store.
- Primary and Secondary Cache Identical in both models



Performance

Run time of a program (ignoring I/O stalls):

- $Run\ time = instruction\ count * CPI * Clock\ Rate$

CPI: Clocks Per Instruction

- $CPI = CPU\ clock\ cycles$
+ $(Avg_memory\ accesses * Avg.\ memory\ latency)$

Average memory Latency at i -th level of memory hierarchy

- $Avg.\ Memory\ Latency_i = (hit\ latency_i * hit\ rate_i)$
+ $[miss\ penalty_i * (1 - hit\ rate_i)]$

Miss penalty:

- $miss\ penalty_i = Average\ Latency_{i-1}$
- $miss\ penalty_0 = Latency_{backing\ store}$



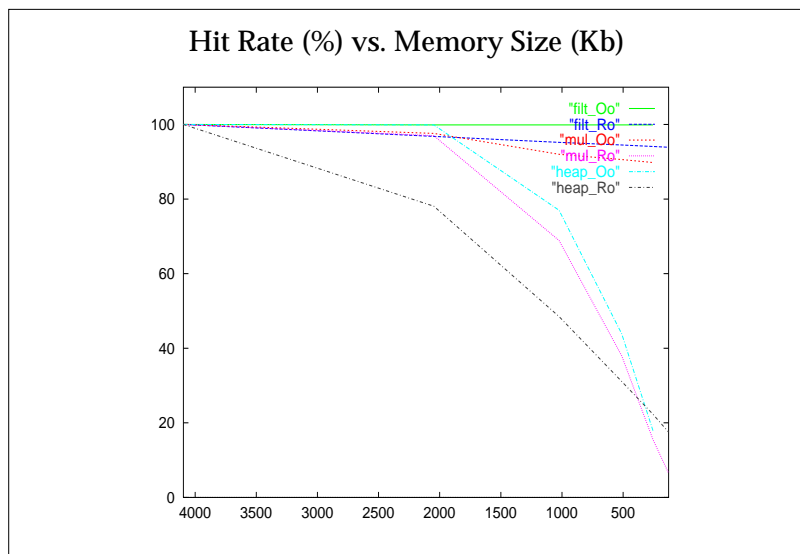
Electronic Memory Simulation Parameters

Cache Level	Size	Lines	Line Size	Hit Latency	Miss Penalty
primary	256 Kb	4096	64 bytes	10 ns	(secondary access)
secondary	1 Mb	4096	256 bytes	50 ns	(main memory access)
main memory	64 Mb-to 128 Kb	32K-to-64	2048 bytes	100ns	(disk access)
disk	Seek + Transfer (avg=1ms)				

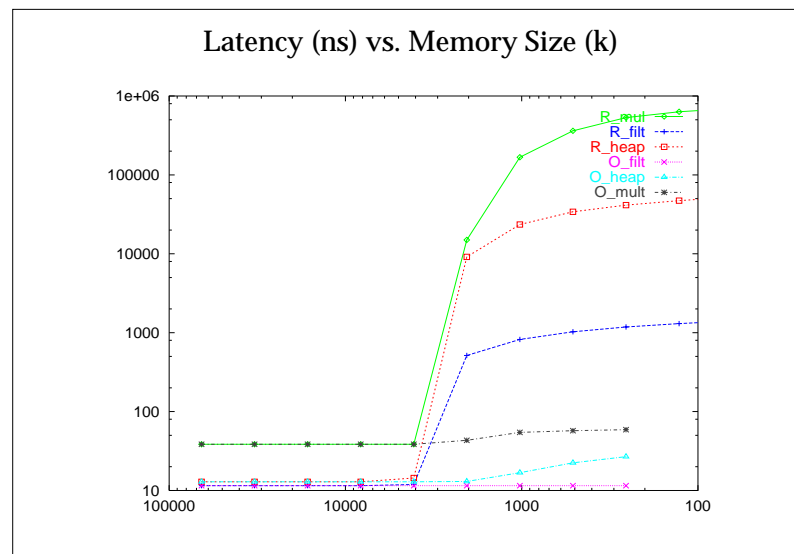
Optoelectronic Memory Simulation Parameters

Cache Level	Size	Lines	Line Size	Hit Latency	Miss Penalty
primary	128 Kb	4096	16 bytes	10 ns	(secondary access)
secondary	1 Mb	4096	64 bytes	50 ns	(main memory access)
opto-cache	64Mb-to 256Kb	512-to-2	128Kb	100ns	(optical memory access)
optical memory					1000 ns





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Research Issues

- What are the appropriate technologies for both the optical memories and the smart pixels used in the cache?
- What are appropriate line sizes, based on current, or near term, fabrication technology?
- What level of internal fragmentation can be tolerated given the lowered fault costs and the limitations on electronic density?
- Given the potential for lowered fault cost, what existing or new address translation mechanisms are best used in this context?
- Given a large line size for the optoelectronic cache, how does this effect the replacement algorithm? Is it possible to devise a new algorithm in which cache lines are overlapped or partially replaced?
- In a multiprocessor application, how should the memory be organized for parallel electronic access relative to the optical memory word size?
- How do the characteristics of the optical memory effect coherency algorithms?
- How do the characteristics of the optical memory effect write policy?

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Conclusions

- Smart Pixel Arrays configured as optoelectronic cache memories can be used to effectively interface a low latency optical backing store for an optoelectronic memory hierarchy.
- Although line sizes in the cache are typically larger than disk-pages, average memory latency is not adversely affected by the additional internal fragmentation introduced.
- Performance gains of 3 to 4 orders of magnitude are possible with near term technology.

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